ERRATA

Erratum: Experimental evidence for Coulomb charging effects in submicron Bi-2212 stacks [JETP Lett. 69, No. 1, 84–90 (10 January 1999)]

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For technical reasons, the reproduction quality of the oscillograms was unsatisfactory.

The editorial board apologizes to the authors and readers and reproduces the figures here. These same figures can be seen at cond-mat./9903134.

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FIG. 1. Stages of the stack fabrication with FIB (a), FIB combined with ion milling (b), a schematic view (c), and a micrograph of the submicron Bi-2212 stacked junction (d).

FIG. 2. The I - V characteristics of the Bi-2212 stacks on a large current and voltage scale: (1) #2, $S=2\ \mu\text{m}^2$; (b) #4, $S=0.6\ \mu\text{m}^2$; (c) #6, $S=0.3\ \mu\text{m}^2$. $T=4.2\ \text{K}$.

FIG. 3. The I - V characteristics of the Bi-2212 stacks on a small current and voltage scale: (1) #2, $S=2\mu\text{ m}^2$; (b) #4, $S=0.6\mu\text{ m}^2$; (c) #6, $S=0.3\mu\text{ m}^2$. $T=4.2\text{ K}$.

FIG. 4. Temperature evolution of the periodic structure on the I - V characteristics (a) and the temperature dependence of the zero-bias resistance R_0 (b) of Bi-2212 stack #6, $S = 0.3 \mu\text{m}^2$.